

EVVOSEMI[®]

THINK CHANGE DO



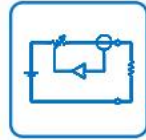
ESD



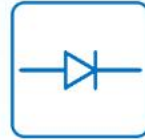
TVS



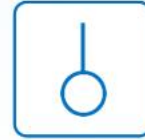
MOS



LDO



Diode



Sensor



DC-DC

Product Specification

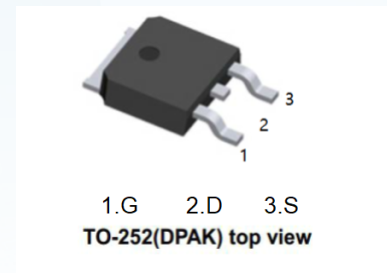
▶ Domestic	Part Number	NTD2955T4G
▶ Overseas	Part Number	NTD2955T4G
▶ Equivalent	Part Number	NTD2955T4G

EV is the abbreviation of name EVVO

-60V P-Channel MOSFET

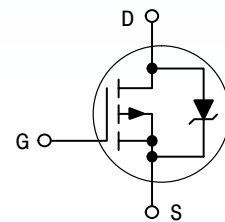
General Description

This Power MOSFET is designed to withstand high energy in the avalanche and commutation modes. Designed for low-voltage, high-speed switching applications in power supplies, converters, and power motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer an additional safety margin against unexpected voltage transients.



Features

- V_{DS} (V) = -60V
- $R_{DS(on)} = 150 \text{ m}\Omega$ ($V_{GS} = -10\text{V}$)
- $I_D = -12\text{A}$ ($V_{GS} = -10\text{V}$)
- Avalanche Energy Specified
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperature
- Designed for Low-Voltage, High-Speed Switching Applications and to Withstand High Energy in the Avalanche and Commutation Modes



MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-60	Vdc
Gate-to-Source Voltage	V_{GS}	± 20	Vdc
- Continuous	V_{GS}	± 25	Vpk
- Non-repetitive ($t_p \leq 10 \text{ ms}$)	V_{GSM}		
Drain Current	I_D	-12	A dc
- Continuous @ $T_a = 25^\circ\text{C}$	I_{DM}	-36	A pk
- Single Pulse ($t_p \leq 10 \text{ ms}$)			
Total Power Dissipation @ $T_a = 25^\circ\text{C}$	P_D	55	W
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy - Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 25 \text{ Vdc}$, $V_{GS} = 10 \text{ Vdc}$, Peak $I_L = 12 \text{ Apk}$, $L = 3.0 \text{ mH}$, $R_G = 25 \Omega$)	E_{AS}	216	mJ
Thermal Resistance	$R_{\theta JC}$	2.73	$^\circ\text{C/W}$
- Junction-to-Case	$R_{\theta JA}$	71.4	
- Junction-to-Ambient (Note 1)	$R_{\theta JA}$	100	
- Junction-to-Ambient (Note 2)			
Maximum Lead Temperature for Soldering Purposes, 1/8 in. from case for 10 seconds	T_L	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. When surface mounted to an FR4 board using 1 in pad size (Cu area = 1.127 in²).
2. When surface mounted to an FR4 board using the minimum recommended pad size (Cu area = 0.412 in²).

-60V P-Channel MOSFET
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Breakdown Voltage (Note 3) (V _{GS} = 0 Vdc, I _D = -0.25 mA) (Positive Temperature Coefficient)	V _{(BR)DSS}	-60 -	- 67		Vdc mV/°C
Zero Gate Voltage Drain Current (V _{GS} = 0 Vdc, V _{DS} = -60 Vdc, T _J = 25°C) (V _{GS} = 0 Vdc, V _{DS} = -60 Vdc, T _J = 150°C)	I _{DSS}			-10 -100	μAdc
Gate-Body Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0 Vdc)	I _{GSS}			-100	nAdc

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = -250 μAdc) (Negative Temperature Coefficient)	V _{GS(th)}	-1.1	-2.0	-3.0	Vdc mV/°C
Static Drain-Source On-State Resistance (V _{GS} = -10 Vdc, I _D = -6.0 Adc)	R _{DS(on)}		150	170	mΩ
Drain-to-Source On-Voltage (V _{GS} = -10 Vdc, I _D = -12 Adc) (V _{GS} = -10 Vdc, I _D = -6.0 Adc, T _J = 150°C)	V _{DS(on)}		-1.86 -	-2.6 -2.0	Vdc
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 6.0 Adc)	g _{FS}		8.0		Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = -25 Vdc, V _{GS} = 0 Vdc, F = 1.0 MHz)	C _{iss}		500	750	pF
Output Capacitance		C _{oss}		150	250	
Reverse Transfer Capacitance		C _{rss}		50	100	

SWITCHING CHARACTERISTICS (Notes 3 and 4)

Turn-On Delay Time	(V _{DD} = -30 Vdc, I _D = -12 A, V _{GS} = -10 V, R _G = 9.1 Ω)	t _{d(on)}		10	20	ns
Rise Time		t _r		45	85	
Turn-Off Delay Time		t _{d(off)}		26	40	
Fall Time		t _f		48	90	
Gate Charge	(V _{DS} = -48 Vdc, V _{GS} = -10 Vdc, I _D = -12 A)	Q _T		15	30	nC
		Q _{GS}		4.0		
		Q _{GD}		7.0		

DRAIN-SOURCE DIODE CHARACTERISTICS (Note 3)

Diode Forward On-Voltage (I _S = 12 Adc, V _{GS} = 0 V) (I _S = 12 Adc, V _{GS} = 0 V, T _J = 150°C)	V _{SD}			-1.6 -1.3	-2.5 -	Vdc
Reverse Recovery Time (I _S = 12 A, dI _S /dt = 100 A/μs, V _{GS} = 0 V)	t _{rr}			50		ns
	t _a			40		
	t _b			10		
Reverse Recovery Stored Charge	Q _{RR}			0.10		μC

3. Indicates Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperature.

-60V P-Channel MOSFET

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

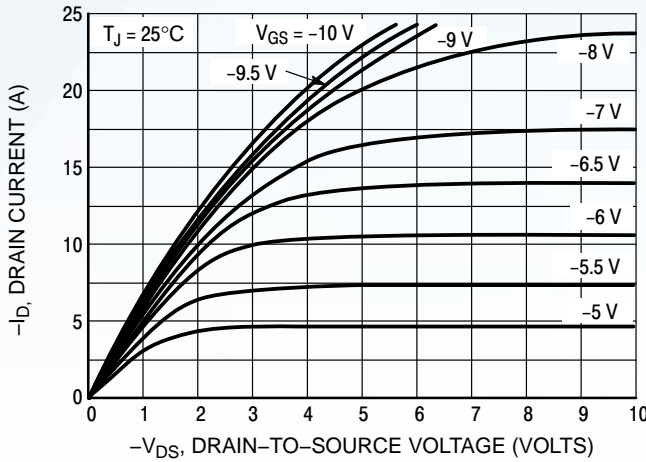


Figure 1. On-Region Characteristics

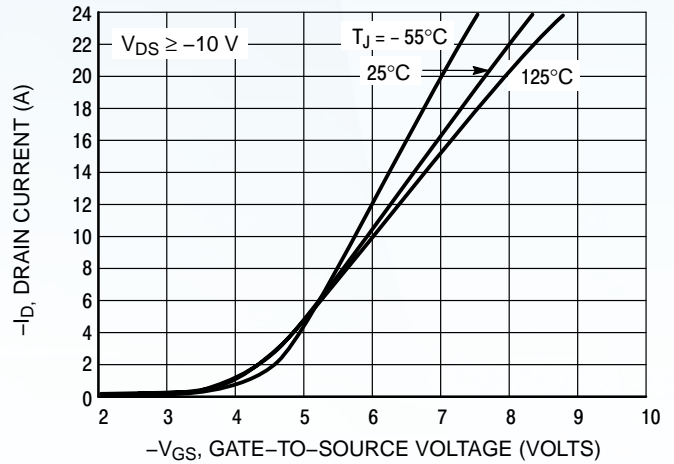


Figure 2. Transfer Characteristics

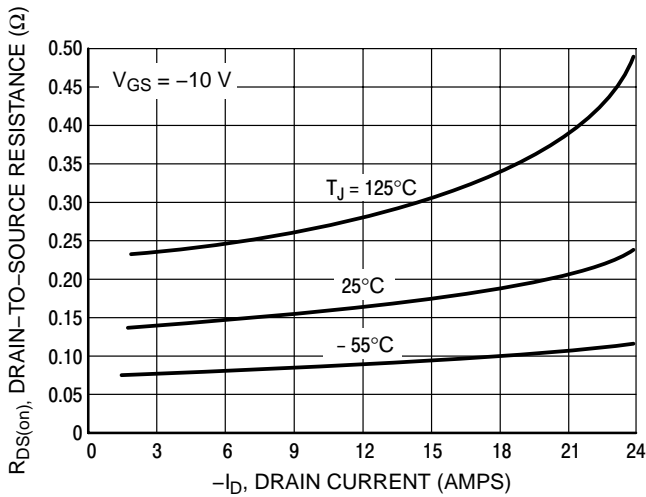


Figure 3. On-Resistance versus Drain Current and Temperature

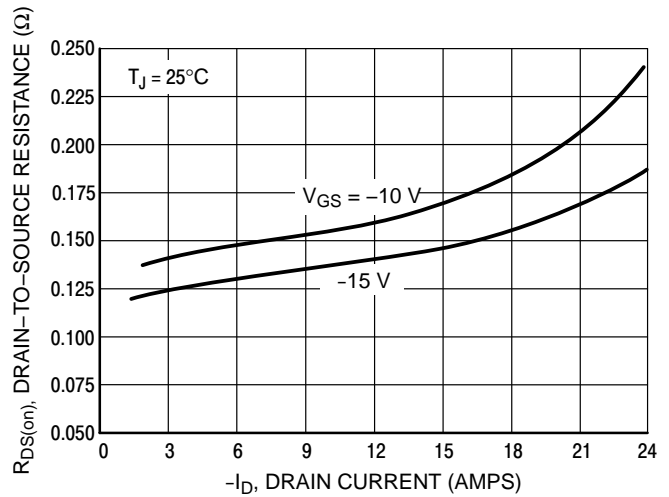


Figure 4. On-Resistance versus Drain Current and Gate Voltage

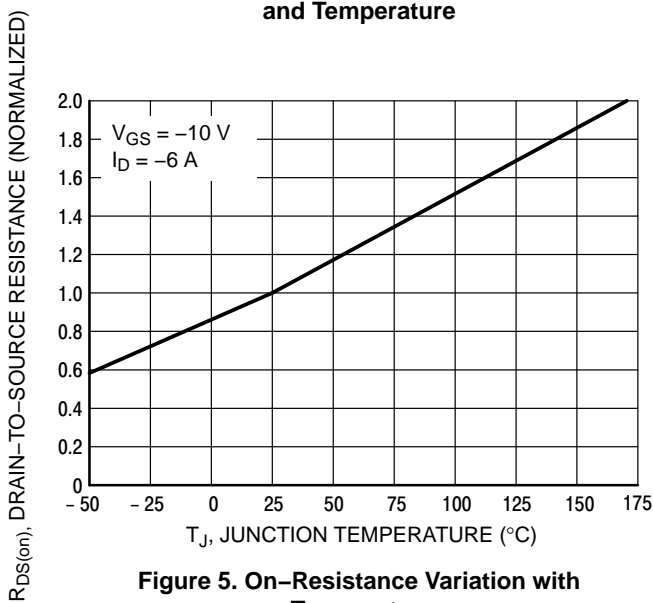


Figure 5. On-Resistance Variation with Temperature

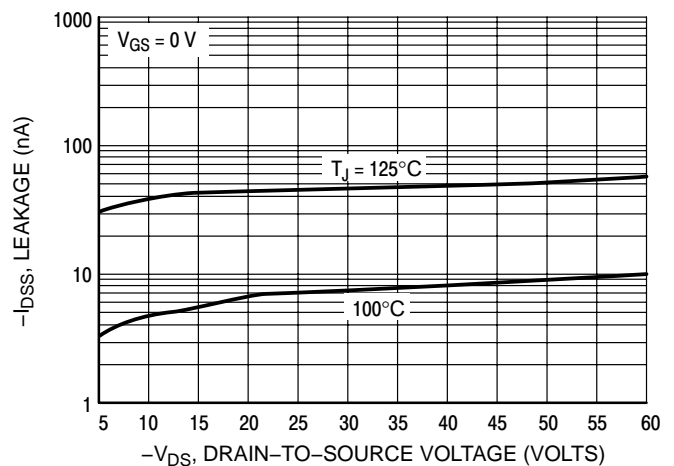


Figure 6. Drain-To-Source Leakage Current versus Voltage

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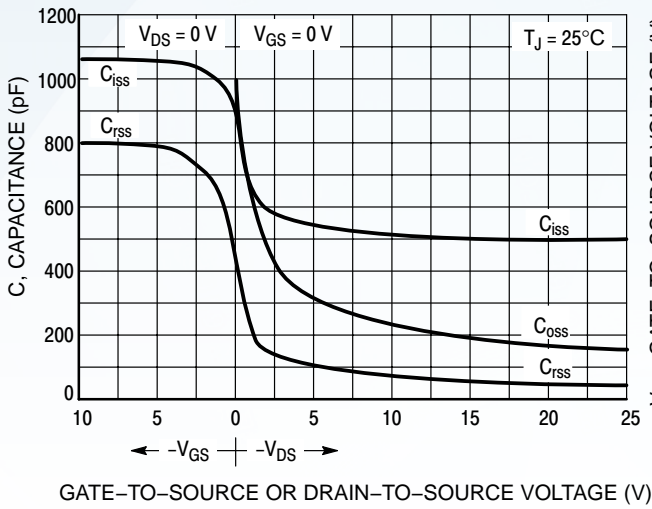


Figure 7. Capacitance Variation

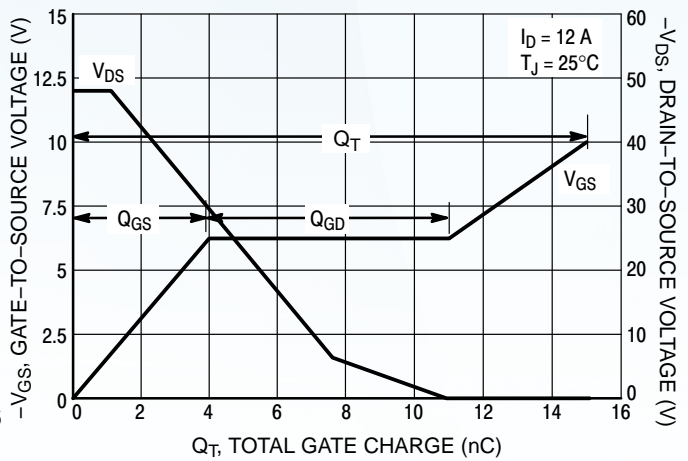


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

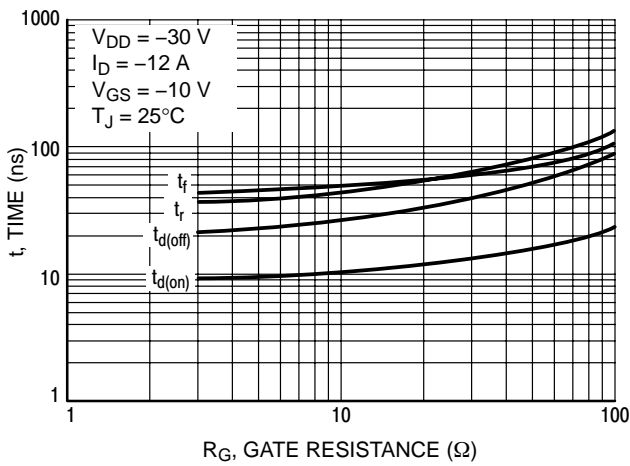


Figure 9. Resistive Switching Time Variation versus Gate Resistance

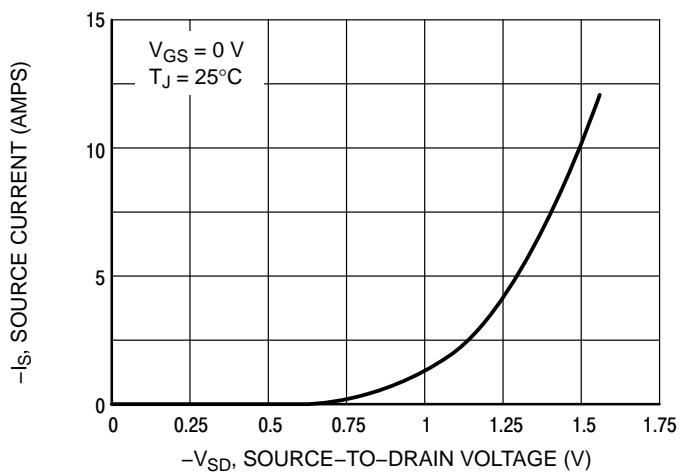


Figure 10. Diode Forward Voltage versus Current

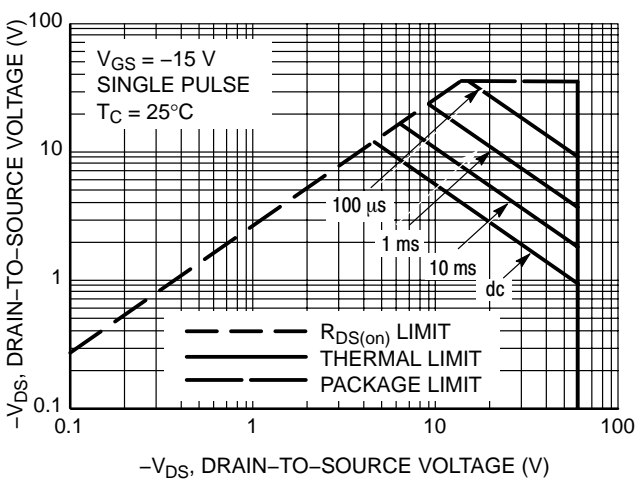


Figure 11. Maximum Rated Forward Biased Safe Operating Area

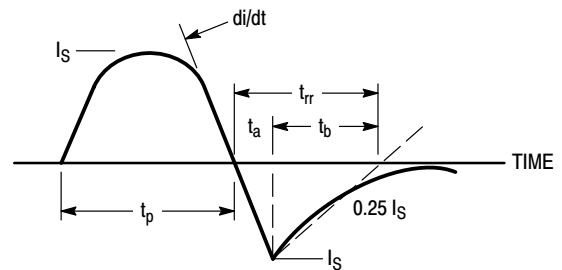


Figure 12. Diode Reverse Recovery Waveform

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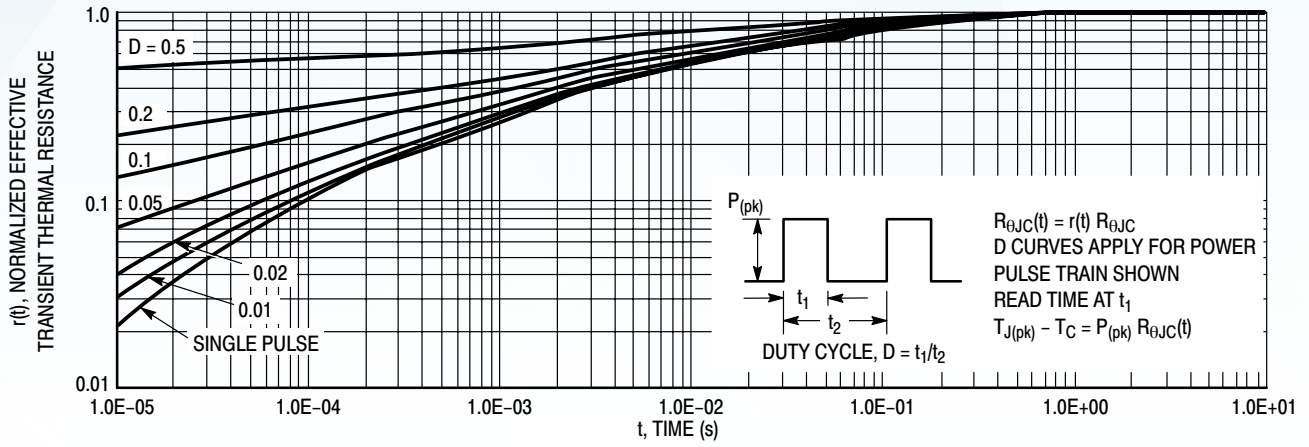
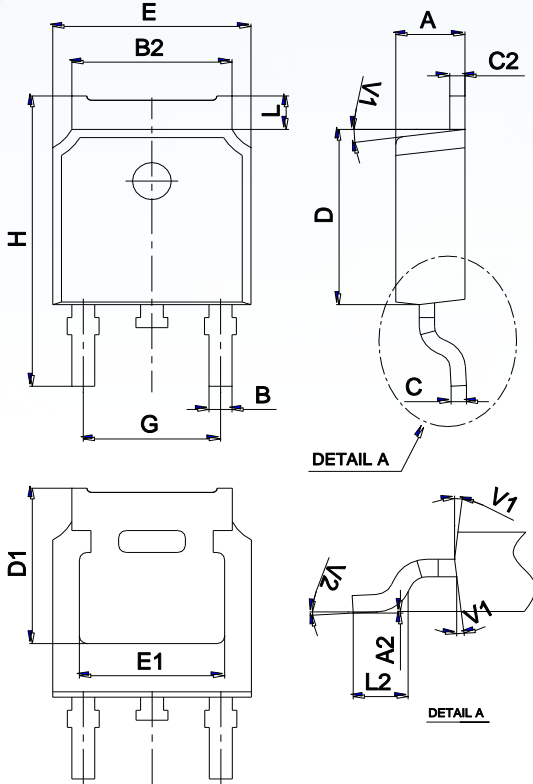


Figure 13. Thermal Response

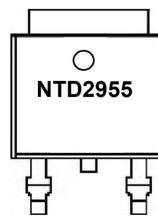
-60V P-Channel MOSFET

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°		0°	6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
NTD2955T4G	TO-252	2500	Tape and reel

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